**Preferred Device** 

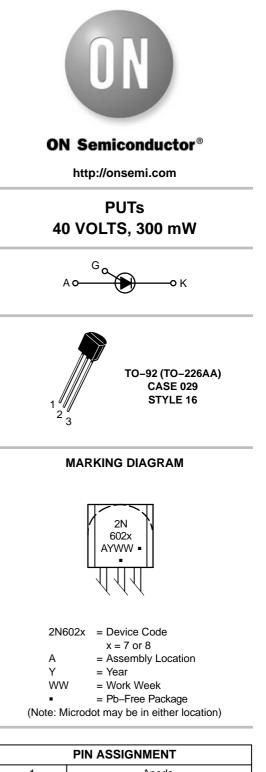
# Programmable Unijunction Transistor

## Programmable Unijunction Transistor Triggers

Designed to enable the engineer to "program" unijunction characteristics such as  $R_{BB}$ ,  $\eta$ ,  $I_V$ , and  $I_P$  by merely selecting two resistor values. Application includes thyristor-trigger, oscillator, pulse and timing circuits. These devices may also be used in special thyristor applications due to the availability of an anode gate. Supplied in an inexpensive TO-92 plastic package for high-volume requirements, this package is readily adaptable for use in automatic insertion equipment.

### Features

- Programmable  $R_{BB}$ ,  $\eta$ ,  $I_V$  and  $I_P$
- Low On–State Voltage 1.5 V Maximum @  $I_F = 50 \text{ mA}$
- Low Gate to Anode Leakage Current 10 nA Maximum
- High Peak Output Voltage 11 V Typical
- Low Offset Voltage 0.35 V Typical ( $R_G = 10 \text{ k}\Omega$ )
- Pb–Free Packages are Available\*



	PIN ASSIGNMENT
1	Anode
2	Gate
3	Cathode

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use

and hest overall value

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Rating		Value	Unit	
Power Dissipation* Derate Above 25°C	P <sub>F</sub> 1/θ <sub>JA</sub>	300 4.0	mW mW/°C	
DC Forward Anode Current* Derate Above 25°C	١ <sub>T</sub>	150 2.67	mA mA/°C	
DC Gate Current*	I <sub>G</sub>	±50	mA	
Repetitive Peak Forward Current 100 μs Pulse Width, 1% Duty Cycle 20 μs Pulse Width, 1% Duty Cycle*	I <sub>TRM</sub>	1.0 2.0	A	
Non–Repetitive Peak Forward Current 10 μs Pulse Width	I <sub>TSM</sub>	5.0	A	
Gate to Cathode Forward Voltage*	V <sub>GKF</sub>	40	V	
Gate to Cathode Reverse Voltage*	V <sub>GKR</sub>	-5.0	V	
Gate to Anode Reverse Voltage*	V <sub>GAR</sub>	40	V	
Anode to Cathode Voltage* (Note 1)	V <sub>AK</sub>	±40	V	
Capacitive Discharge Energy (Note 2)	E	250	μJ	
Power Dissipation (Note 3)	PD	300	mW	
Operating Temperature	T <sub>OPR</sub>	-50 to +100	°C	
Junction Temperature	TJ	-50 to +125	°C	
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*Indicates JEDEC Registered Data 1. Anode positive,  $R_{GA} = 1000 \Omega$ Anode negative,  $R_{GA} = open$ 2.  $E = 0.5 \cdot CV^2$  capacitor discharge energy limiting resistor and repetition. 3. Derate current and power above 25°C.

### THERMAL CHARACTERISTICS

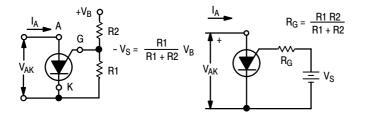
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	75	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	200	°C/W
Maximum Lead Temperature for Soldering Purposes (<1/16" from case, 10 seconds maximum)	ΤL	260	°C

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

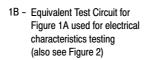
Characteristic		Fig. No.	Symbol	Min	Тур	Max	Unit
Peak Current* (V <sub>S</sub> = 10 Vdc, R <sub>G</sub> = 1 MΩ) (V <sub>S</sub> = 10 Vdc, R <sub>G</sub> = 10 kΩ)	2N6027 2N6028 2N6027 2N6028	2,9,11	Ι <sub>Ρ</sub>	- - - -	1.25 0.08 4.0 0.70	2.0 0.15 5.0 1.0	μΑ
Offset Voltage* $(V_S = 10 \text{ Vdc}, R_G = 1 \text{ M}\Omega)$ $(V_S = 10 \text{ Vdc}, R_G = 10 \text{ k}\Omega)$	2N6027 2N6028 (Both Types)	1	V <sub>T</sub>	0.2 0.2 0.2	0.70 0.50 0.35	1.6 0.6 0.6	V
Valley Current* (V <sub>S</sub> = 10 Vdc, R <sub>G</sub> = 1 MΩ) (V <sub>S</sub> = 10 Vdc, R <sub>G</sub> = 10 k Ω) (V <sub>S</sub> = 10 Vdc, R <sub>G</sub> = 200 Ω)	2N6027 2N6028 2N6027 2N6028 2N6027 2N6028	1,4,5	Ιv	- 70 25 1.5 1.0	18 18 150 150 - -	50 25 - - - -	μA mA
Gate to Anode Leakage Current* $(V_S = 40 \text{ Vdc}, T_A = 25^{\circ}\text{C}, \text{ Cathode Open})$ $(V_S = 40 \text{ Vdc}, T_A = 75^{\circ}\text{C}, \text{ Cathode Open})$		-	I <sub>GAO</sub>		1.0 3.0	10 -	nAdc
Gate to Cathode Leakage Current (V <sub>S</sub> = 40 Vdc, Anode to Cathode Shorted)		-	I <sub>GKS</sub>	-	5.0	50	nAdc
Forward Voltage* (I <sub>F</sub> = 50 mA Peak) (Note 4)		1,6	V <sub>F</sub>	-	0.8	1.5	V
Peak Output Voltage* (V <sub>G</sub> = 20 Vdc, C <sub>C</sub> = 0.2 $\mu$ F)		3,7	Vo	6.0	11	_	V
Pulse Voltage Rise Time $(V_B = 20 \text{ Vdc}, C_C = 0.2 \mu\text{F})$		3	t <sub>r</sub>	-	40	80	ns

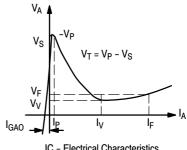
\*Indicates JEDEC Registered Data

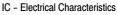
4. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2%.

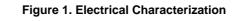


1A - Programmable Unijunction with "Program" Resistors R1 and R2









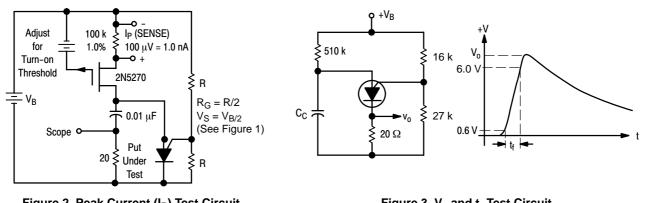
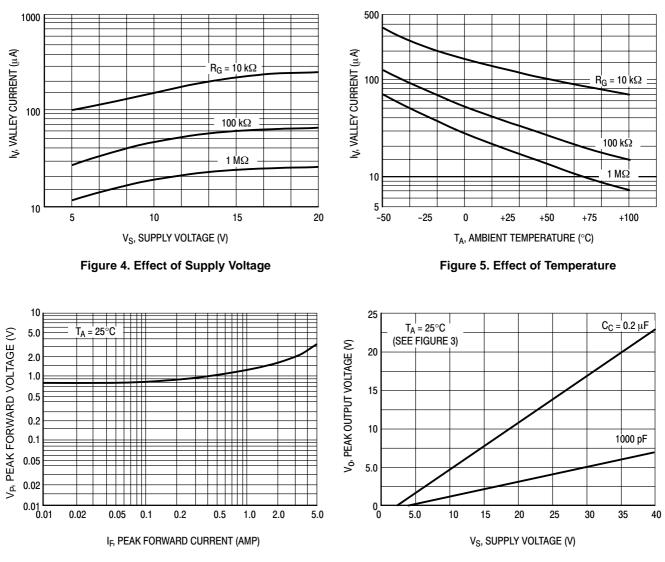


Figure 2. Peak Current (IP) Test Circuit

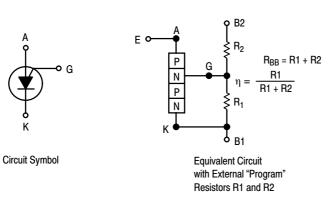
Figure 3.  $V_{o}$  and  $t_{r}$  Test Circuit

### **TYPICAL VALLEY CURRENT BEHAVIOR**







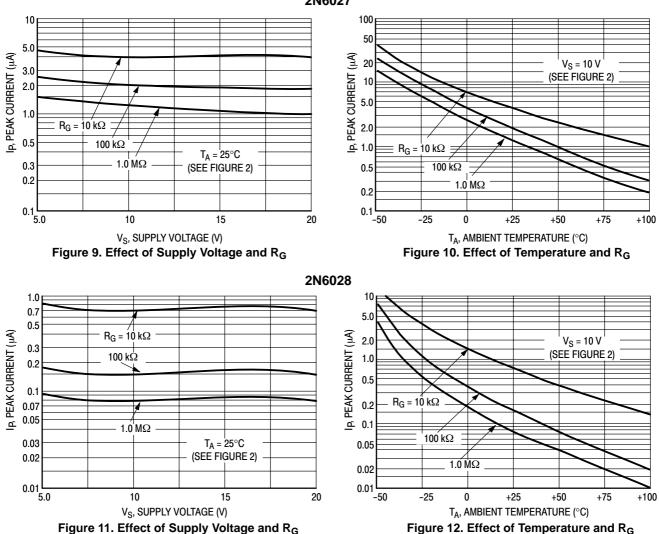


C<sub>C</sub> H<sub>T</sub> H<sub>2</sub> + C<sub>C</sub> H<sub>1</sub> H<sub>2</sub> + Typical Application

Figure 8. Programmable Unijunction

### **TYPICAL PEAK CURRENT BEHAVIOR**

2N6027



#### **ORDERING INFORMATION**

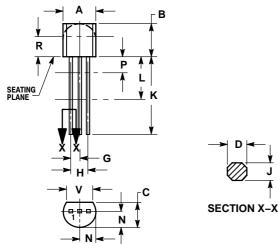
U.S.	European Equivalent	Shipping <sup>†</sup>	Description of TO-92 Tape Orientation		
2N6027					
2N6027G					
2N6028		5000 Units / Box	N/A – Bulk		
2N6028G					
2N6027RLRA	_				
2N6027RLRAG	2N6027RL1				
2N6028RLRA	2N6027RL1G	2000 / Tape & Reel	Round side of TO–92 and adhesive tape visible		
2N6028RLRAG	_				
2N6028RLRM	_				
2N6028RLRMG	_	2000 / Tana & Amma Day	Flat side of TO–92 and adhesive tape visible		
2N6028RLRP		2000 / Tape & Ammo Box	Deved side of TO 02 and adhesive taxes visible		
2N6028RLRPG			Round side of TO–92 and adhesive tape visible		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*The "G" suffix indicates Pb-Free package available.

#### PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 029-11 **ISSUE AL** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 1.
- 2.
- CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R 3.
- IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND 4 BEYOND DIMENSION K MINIMUM

MIN 0.175 0.170	MAX 0.205	MIN 4.45	MAX
0.170		4 45	
	0.010		5.20
0 105	0.210	4.32	5.33
0.125	0.165	3.18	4.19
0.016	0.021	0.407	0.533
0.045	0.055	1.15	1.39
0.095	0.105	2.42	2.66
0.015	0.020	0.39	0.50
0.500		12.70	
0.250		6.35	
0.080	0.105	2.04	2.66
	0.100		2.54
0.115		2.93	
0.135		3.43	
	0.045 0.095 0.015 0.500 0.250 0.080  0.115	0.045  0.055    0.095  0.105    0.015  0.020    0.500     0.250     0.080  0.105     0.100    0.115	0.045  0.055  1.15    0.095  0.105  2.42    0.015  0.020  0.39    0.500   12.70    0.250   6.35    0.080  0.105  2.04     0.105  2.04     0.105  2.04     0.100     0.115   2.93

PIN 1 ANODE

GATE 2.

3. CATHODE

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